

International Workshop on Advanced Materials and Devices II
Osaka Umekita Knowledge Center

Workshop Program (September 4, 2015)

13:00 – 13:10 Opening remark

Session I: Chair Prof. Shigehiko Sasa

13:10 – 14:00 **Millimeter-wave GaN HEMTs on silicon and on silicon carbide:** Prof. Colombo Bolognesi (Swiss Federal Institute of Technology: ETH-Zürich)

14:00 – 14:50 **Challenge and outlook of gallium oxide power devices:** Dr. Masataka Higashiwaki (National Institute of Information and Communications Technology: NICT)

14:50 – 15:20 Break (Poster viewing)

Session II: Chair Prof. Mitsuaki Yano

15:20 – 16:10 **Growth of oxide semiconductors by mist CVD:** Prof. Shizuo Fujita (Kyoto University)

16:10 – 16:30 **Molecular beam epitaxial growth and characterization of transition metal oxide WO₃ films:** Prof. Kazuto Koike (Osaka Institute of Technology: OIT)

Session III: Chair Prof. Toshihiko Maemoto

16:30 – 17:20 **Self-switching diodes as THz detectors and emitters:** Prof. Thomas Gonzalez (Salamanca University)

17:20 – 17:40 **Materials and devices for secure life systems:** Prof. Shigehiko Sasa (OIT)